Applicants have amended Claim 28 in accordance with the Examiner's suggestion. Accordingly, it is requested that this rejection be withdrawn.

Claim Rejection – 35 USC §102

The Examiner also rejects Claims 1-4, 8, 10-13, 17, 19-21, 25, 27-30 and 34 under 35 USC §102(e) as being anticipated by Kanoh et al. This rejection is respectfully traversed.

In order to advance the prosecution of this application, Applicants have amended each of the independent claims (i.e. Claims 1, 10, 19 and 27) to include the feature wherein the interlayer insulating film comprises a resin film having a viscosity of 10 cp or more. This feature is supported, for example, by page 10, lns. 24-25 in the specification of the present application.

Applicants respectfully submit that Kanoh does not disclose or suggest this feature. Accordingly, the independent claims, and those claims dependent thereon, of the present application are patentable over this reference. Therefore, it is requested that this rejection be withdrawn.

Claim Rejections – 35 USC §103

The Examiner also rejects Claims 9, 18, 26 and 35 under 35 USC §103 as being unpatentable over Kanoh et al. together with Yamazaki et al. This rejection is also respectfully traversed.

For at least the reasons discussed above for the independent claims, the cited references do not disclose or suggest the semiconductor device of these dependent claims. Accordingly, it is requested that this rejection be withdrawn.

IDS

Applicants filed an IDS on December 20, 2002. It does not appear that the Examiner considered this IDS when issuing the pending office action. Applicants request that the Examiner consider this IDS and initial the 1449 form prior to issuing any further actions on this application.

Conclusion

Applicants respectfully submit that the present application is now in a condition for allowance.

If any fee is due for this amendment, please charge our deposit account 50/1039.

Favorable reconsideration is earnestly solicited.

Respectfully submitted,

Date: May 1, 2003

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Marked-up copy of the claims as amended:

IN THE CLAIMS:

Please amend the claims as follows:

1.(Amended) A semiconductor device comprising:

a thin film transistor comprising a semiconductor layer [on an insulating surface, an insulating film on said semiconductor layer] over a substrate and a gate electrode [on said insulating film] with an insulating film interposed therebetween;

a plurality of projected portions [on said insulating surface] over said substrate;

an interlayer insulating film covering said thin film transistor and said plurality of projected portions, said interlayer insulating film having a projected and recessed surface, and said interlayer insulating film comprising a resin film having a viscosity of 10 cp or more; and

a pixel electrode electrically connected to said thin film transistor, said pixel electrode having a projected and recessed surface on said interlayer insulating film.

10.(Amended) A semiconductor device comprising:

a thin film transistor comprising a semiconductor layer on an insulating surface, an insulating film on said semiconductor layer and a gate electrode on said insulating film;

a plurality of projected portions on said insulating surface; [and]

an interlayer insulating film covering said thin film transistor and said plurality of projected portions, said interlayer insulating film having a projected and recessed surface, and said interlayer insulating film comprising a resin film having a viscosity of 10 cp or more; and

a pixel electrode [in contact with said projected portions, said pixel electrode] having a projected and recessed surface on said interlayer insulating film, and electrically connected to said thin film transistor.

19.(Amended) A semiconductor device comprising:

a thin film transistor comprising a semiconductor layer [on an insulating surface, an insulating film on said semiconductor layer] over a substrate and a gate electrode [on said insulating film] with an insulating film interposed therebetween;

a plurality of projected portions [on said insulating film] over said substrate;

an interlayer insulating film covering said thin film transistor and said plurality of projected portions, said interlayer insulating film having a projected and recessed surface, and said interlayer insulating film comprising a resin film having a viscosity of 10 cp or more; and

a pixel electrode electrically connected to said thin film transistor, said pixel electrode having a projected and recessed surface on said interlayer insulating film.

27.(Amended) A semiconductor device comprising:

a thin film transistor comprising a semiconductor layer on an insulating surface, an insulating film on said semiconductor layer and a gate electrode on said insulating film;

a plurality of projected portions on said insulating film; [and]

an interlayer insulating film covering said thin film transistor and said plurality of projected portions, said interlayer insulating film having a projected and recessed surface, and said interlayer insulating film comprising a resin film having a viscosity of 10 cp or more; and

a pixel electrode [in contact with said projected portions, said pixel electrode] having a projected and recessed surface on said interlayer insulating film, and electrically connected to said thin film transistor.

28.(Amended) The semiconductor device according to claim 27, wherein said projected portions comprise a same material as [one selected from the group consisting of a semiconductor layer,] a gate electrode[, and a gate insulating film] of said thin film transistor.